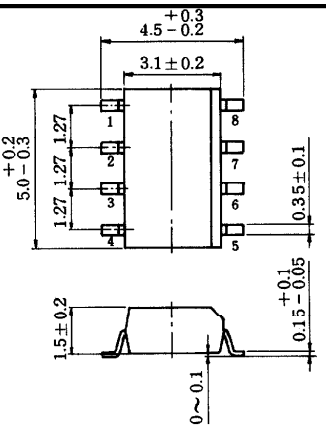
TOSHIBA TRANSISTOR SILICON EPITAXIAL PLANAR TYPE

HN1V02H

AM RADIO BAND TUNING APPLICATIONS.

Unit in mm



- High Capacitance Ratio : C1V / C8V = 19.5 (Typ.)
- High Q : Q = 200 (Min.)
- Including Two Devices in FM8 Package (Flat Pack Mini 8Pin)
- Low Voltage Operation : V_R = 1~8V

1. ANODE 1
2, 7. CATHODE 1
3, 6. CATHODE 2
4. N.C.
5. ANODE 2
8. N.C.

JEDEC	—
EIAJ	—
TOSHIBA	1-5J1B

Weight : 0.05g

MAXIMUM RATINGS (Ta = 25°C) (D_1, D_2)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	16	V
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C) (D_1, D_2)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R = 10μA	16	—	—	V
Reverse Current	I_R	V_R = 16V	—	—	20	nA
Capacitance	C1V	V_R = 1V, f = 1MHz	435	—	540	pF
Capacitance	C3V	V_R = 3V, f = 1MHz	140	—	250	pF
Capacitance	C5V	V_R = 5V, f = 1MHz	50.0	—	90.0	pF
Capacitance	C8V	V_R = 8V, f = 1MHz	19.9	—	26.7	pF
Capacitance Ratio	C1V / C8V	—	16.2	19.5	—	—
Figure of Merit	Q	V_R = 1V, f = 1MHz	200	—	—	—

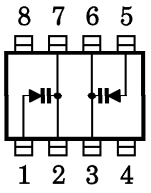
Note 1 : Two Devices in one Package are matched for capacitance to 2.5%.

$$\frac{C\,(Max.) - C\,(Min.)}{C\,(Min.)} \leqq 0.025\ (V_R = 1 \sim 8V)$$

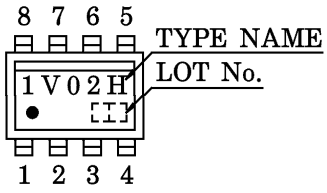
Note 2 : C8V is devided into two classifications as follows.

Classification	C8V (pF)
A	19.9~23.7
B	22.4~26.7

PIN ASSIGNMENT (TOP VIEW)



MARKING



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